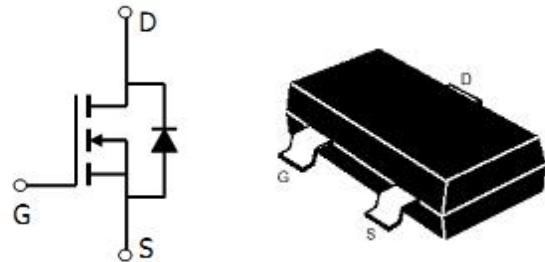


GM3400A

SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)



N-Channel Enhancement-Mode MOS FETs

N 溝道增強型 MOS 場效應管

■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Rat 額定值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	BV_{DSS}	30	V
Gate- Source Voltage 柵極-源極電壓	V_{GS}	± 12	V
Drain Current (continuous) 漏極電流 - 連續	I_D	5.8	A
Drain Current (pulsed) 漏極電流 - 脉冲	I_{DM}	30	A
Total Device Dissipation 總耗散功率 $T_A=25^\circ\text{C}$ 環境溫度為 25°C	P_D	1400	mW
Junction 結溫	T_J	150	$^\circ\text{C}$
Storage Temperature 儲存溫度	T_{stg}	-55 to +150	$^\circ\text{C}$

■DEVICE MARKING 打標

GM3400A=X0

GM3400A

ELECTRICAL CHARACTERISTICS 電特性

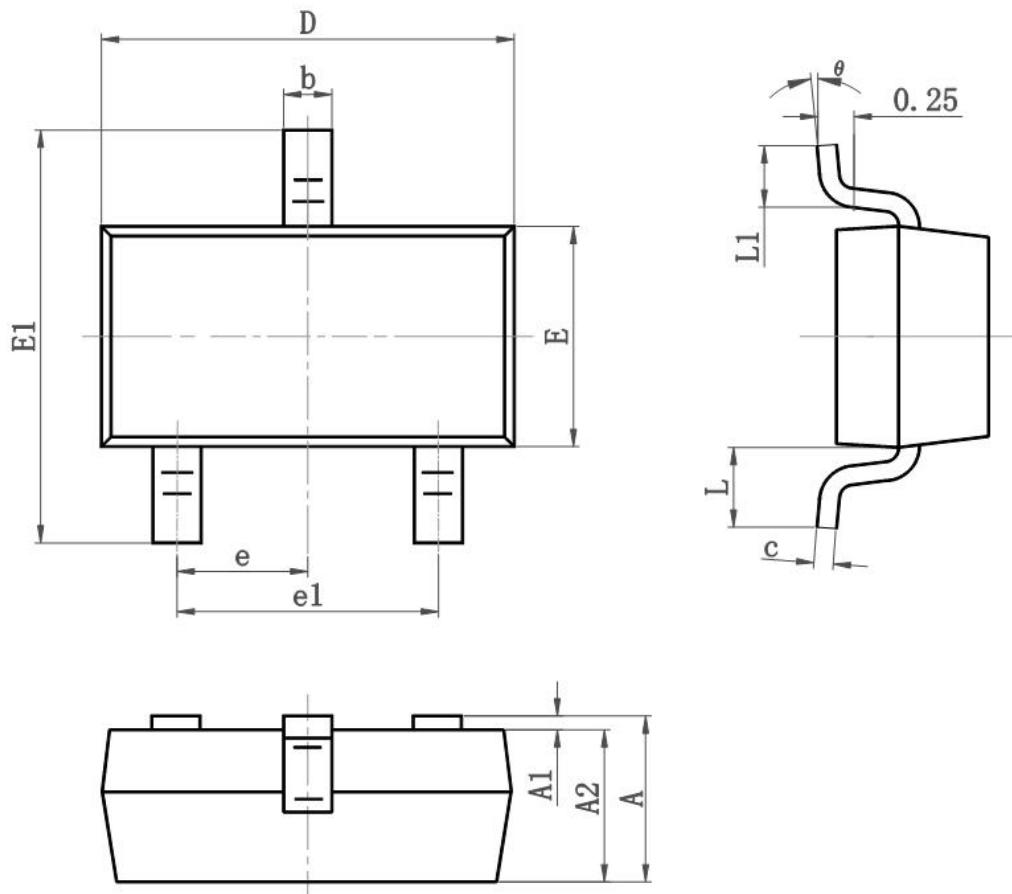
($T_A=25^\circ\text{C}$ unless otherwise noted 如無特殊說明，溫度為 25°C)

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓($I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$)	BV_{DSS}	30	—	—	V
Gate Threshold Voltage 柵極開啓電壓($I_D = 250\mu\text{A}$, $V_{GS} = V_{DS}$)	$V_{GS(\text{th})}$	0.6	—	1.4	V
Diode Forward Voltage Drop 內附二極管正向壓降($I_S = 1.25\text{A}$, $V_{GS} = 0\text{V}$)	V_{SD}	—	0.7	1	V
Zero Gate Voltage Drain Current 零柵壓漏極電流($V_{GS} = 0\text{V}$, $V_{DS} = 30\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 柵極漏電流($V_{GS} = \pm 12\text{V}$, $V_{DS} = 0\text{V}$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D = 5.8\text{A}$, $V_{GS} = 10\text{V}$)	$R_{DS(\text{ON})}$	—	28	30	$\text{m}\Omega$
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D = 5\text{A}$, $V_{GS} = 4.5\text{V}$)	$R_{DS(\text{ON})}$	—	36	40	$\text{m}\Omega$
Static Drain-Source On-State Resistance 静态漏源導通電阻($I_D = 4\text{A}$, $V_{GS} = 2.5\text{V}$)	$R_{DS(\text{ON})}$	—	45	50	$\text{m}\Omega$
Input Capacitance 輸入電容 ($V_{GS} = 0\text{V}$, $V_{DS} = 15\text{V}$, $f = 1\text{MHz}$)	C_{ISS}	—	820	—	pF
Output Capacitance 輸出電容 ($V_{GS} = 0\text{V}$, $V_{DS} = 15\text{V}$, $f = 1\text{MHz}$)	C_{OSS}	—	90	—	pF
Turn-ON Time 开启時間 ($V_{DS} = 15\text{V}$, $V_{GS} = 10\text{V}$, $R_{GEN} = 6\Omega$)	$t_{(\text{on})}$	—	9.6	—	ns
Turn-OFF Time 無斷時間 ($V_{DS} = 15\text{V}$, $V_{GS} = 10\text{V}$, $R_{GEN} = 6\Omega$)	$t_{(\text{off})}$	—	39	—	ns

Pulse Width $\leq 300\ \mu\text{s}$; Duty Cycle $\leq 2.0\%$

GM3400A

■DIMENSION 外形封裝尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.300	1.600	0.050	0.063
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°